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**Nakamura et al.**

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(54) **NON-VOLATILE SEMICONDUCTOR STORAGE DEVICE**

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CPC ..... *G11C 16/0483* (2013.01); *G11C 16/24* (2013.01)

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**Related U.S. Patent Documents**

Reissue of:

(64) Patent No.: **7,911,844**  
Issued: **Mar. 22, 2011**  
Appl. No.: **12/337,808**  
Filed: **Dec. 18, 2008**

(57) **ABSTRACT**

A non-volatile semiconductor storage device includes: a memory cell array having memory cells arranged therein, the memory cells storing data in a non-volatile manner; and a plurality of transfer transistors transferring a voltage to the memory cells, the voltage to be supplied for data read, write and erase operations with respect to the memory cells. Each of the transfer transistors includes: a gate electrode formed on a semiconductor substrate via a gate insulation film; and diffusion layers formed to sandwich the gate electrode therebetween and functioning as drain/source layers. Upper layer wirings are provided above the diffusion layers and provided with a predetermined voltage to prevent depletion of the diffusion layers at least when the transfer transistors become conductive.

U.S. Applications:

(63) Continuation of application No. 14/521,160, filed on Oct. 22, 2014, now Pat. No. Re. 46,526, which is a  
(Continued)

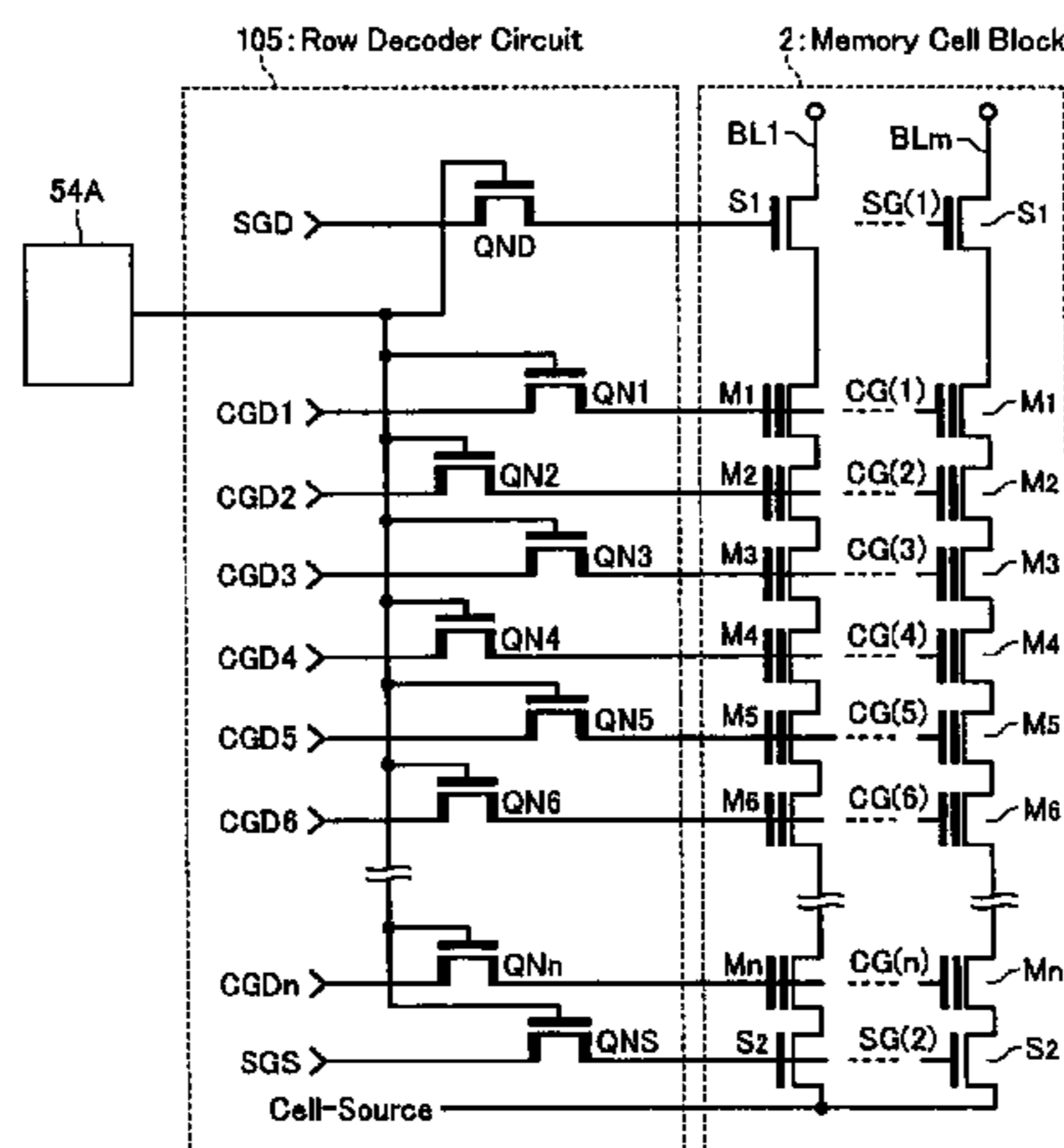
(30) **Foreign Application Priority Data**

Dec. 20, 2007 (JP) ..... 2007-328852

(51) **Int. Cl.**

*G11C 16/04* (2006.01)  
*G11C 16/24* (2006.01)

**10 Claims, 10 Drawing Sheets**



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## Related U.S. Application Data

continuation of application No. 13/848,563, filed on Mar. 21, 2013, now Pat. No. Re. 45,307, which is an application for the reissue of Pat. No. 7,911,844.

### (58) Field of Classification Search

USPC ..... 365/185.17, 185.05, 185.11, 185.12, 365/185.06, 185.18, 185.23, 185.27, 365/185.33, 182, 189.14, 230.02, 230.06

See application file for complete search history.

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FIG. 1

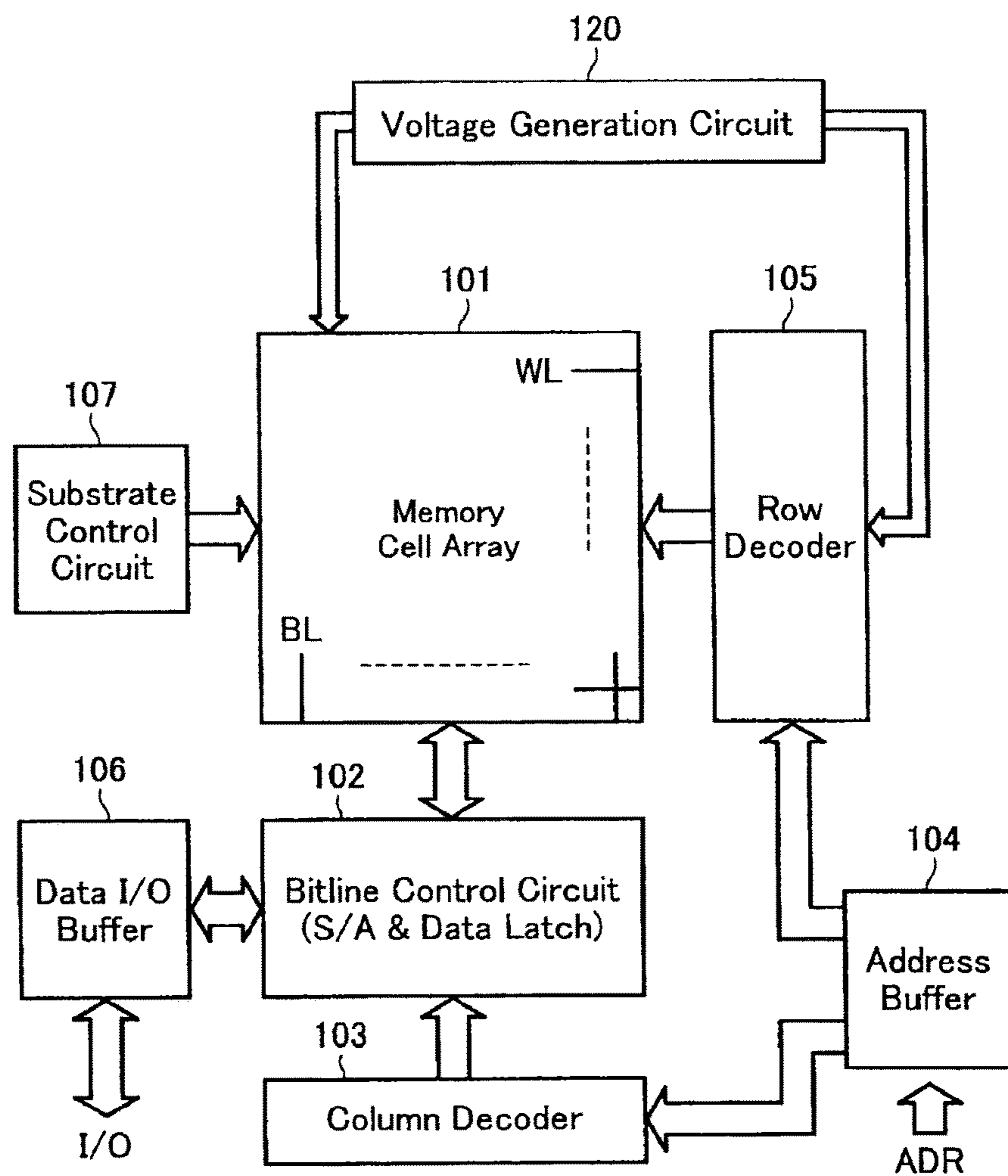


FIG. 2A

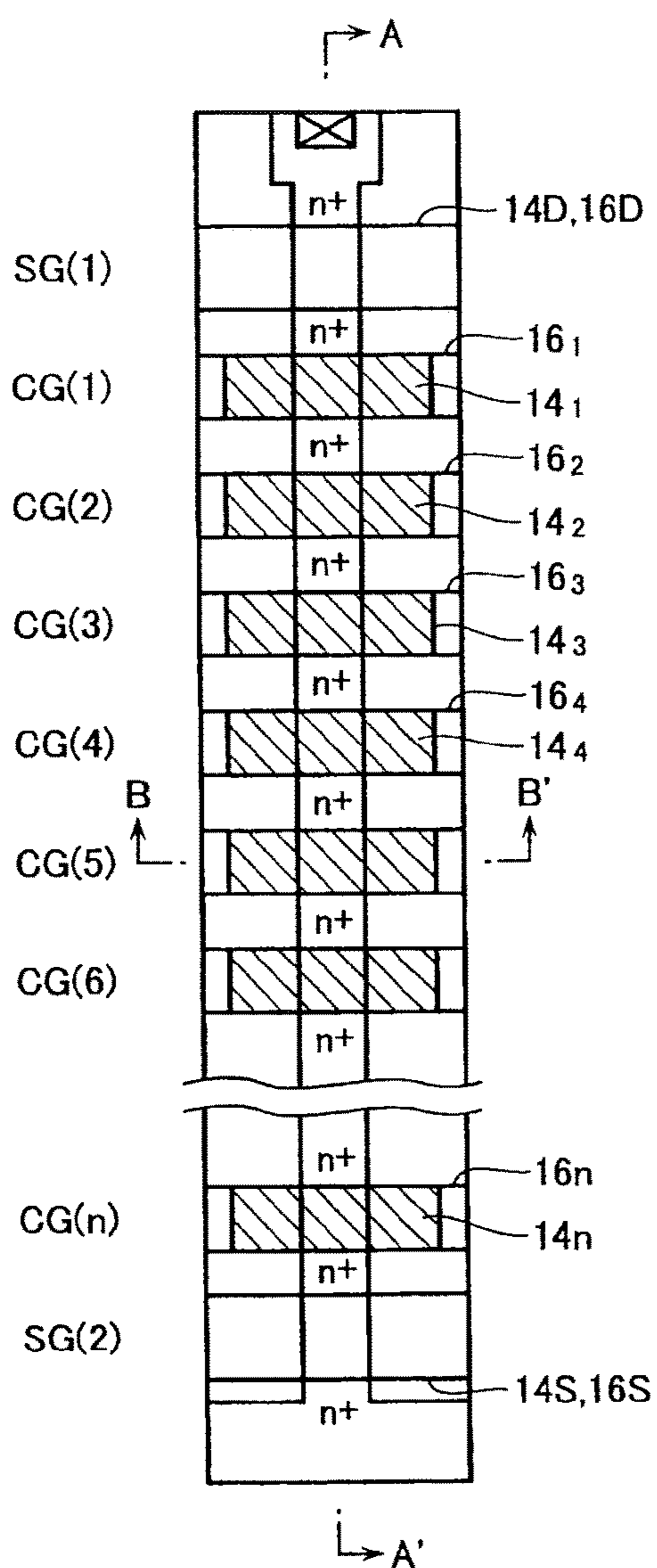


FIG. 2B

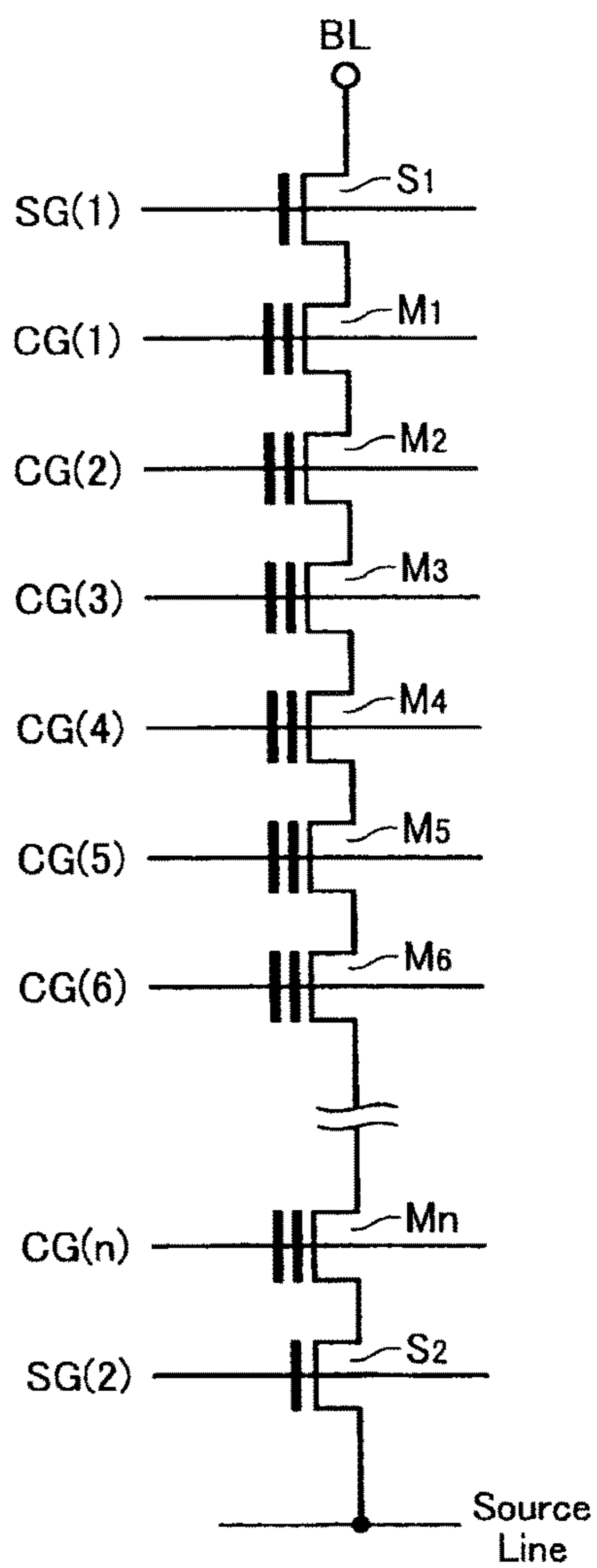




FIG. 3A

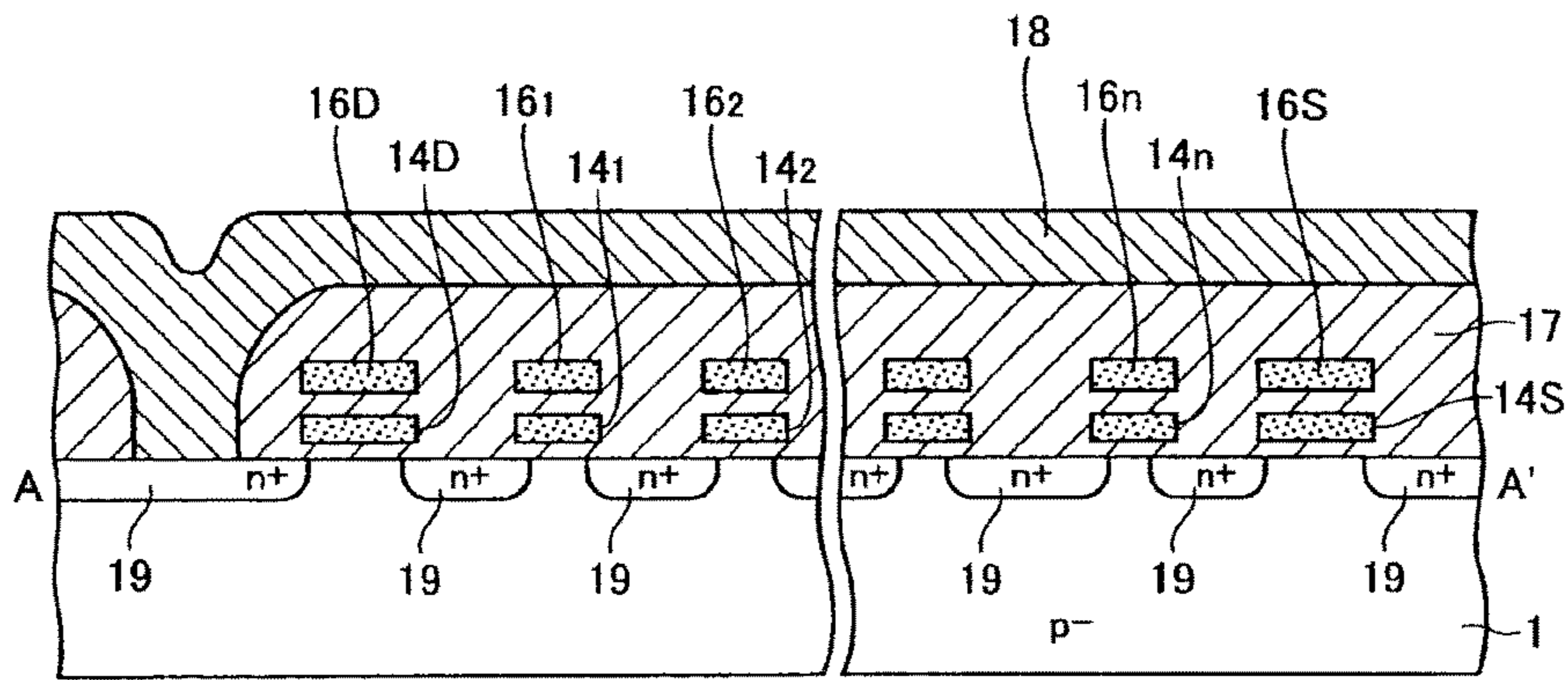


FIG. 3B

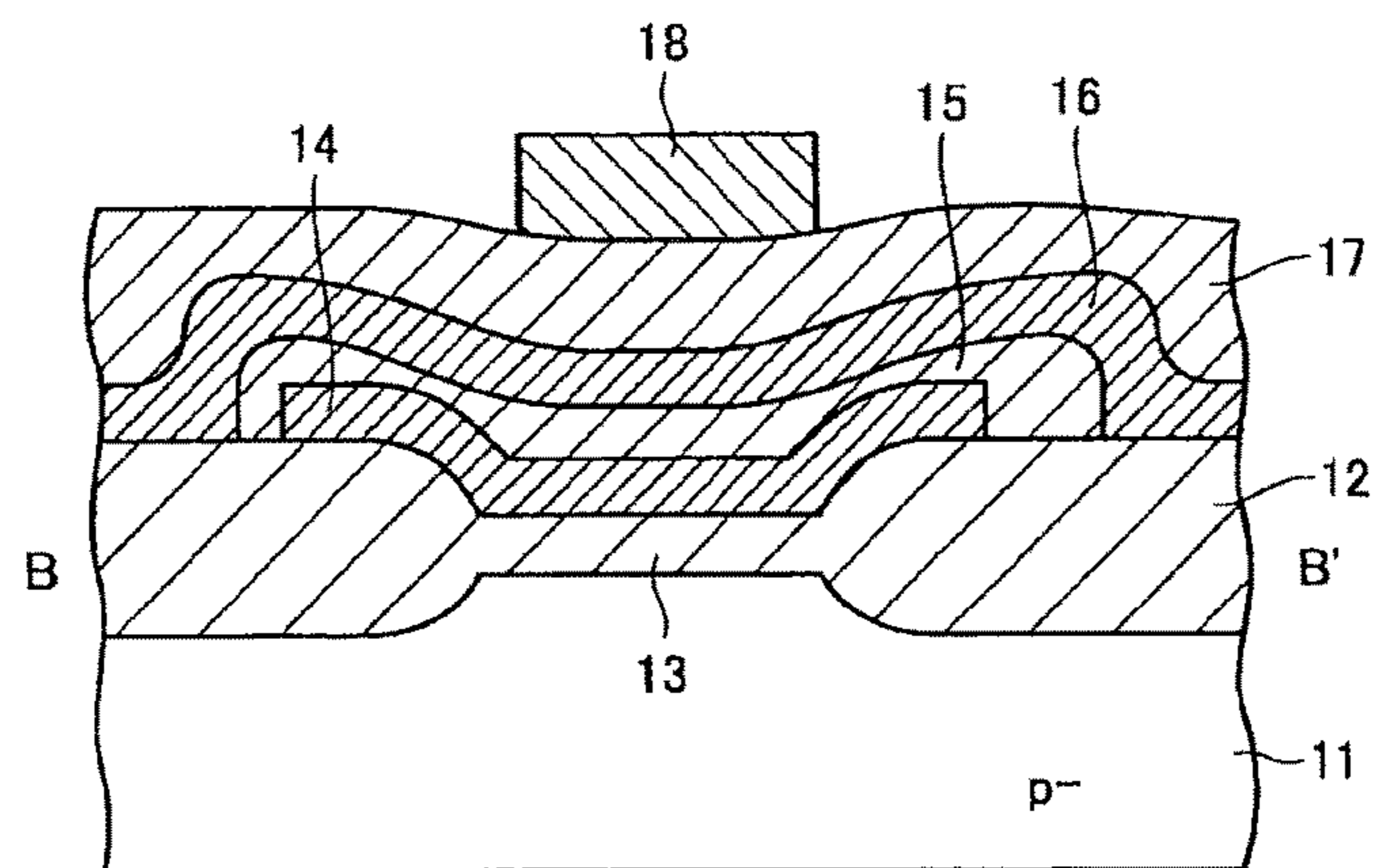


FIG. 4

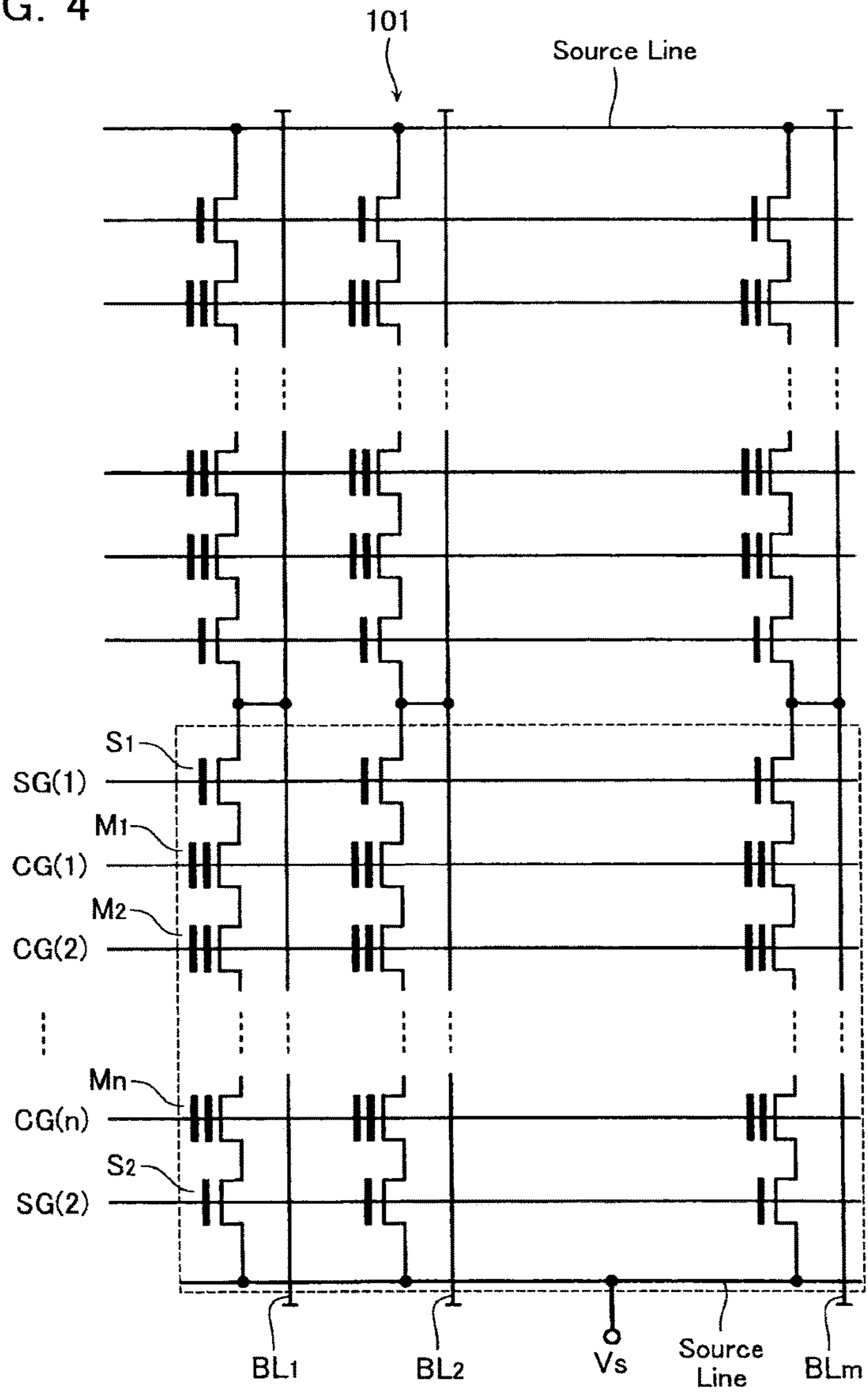


FIG. 5

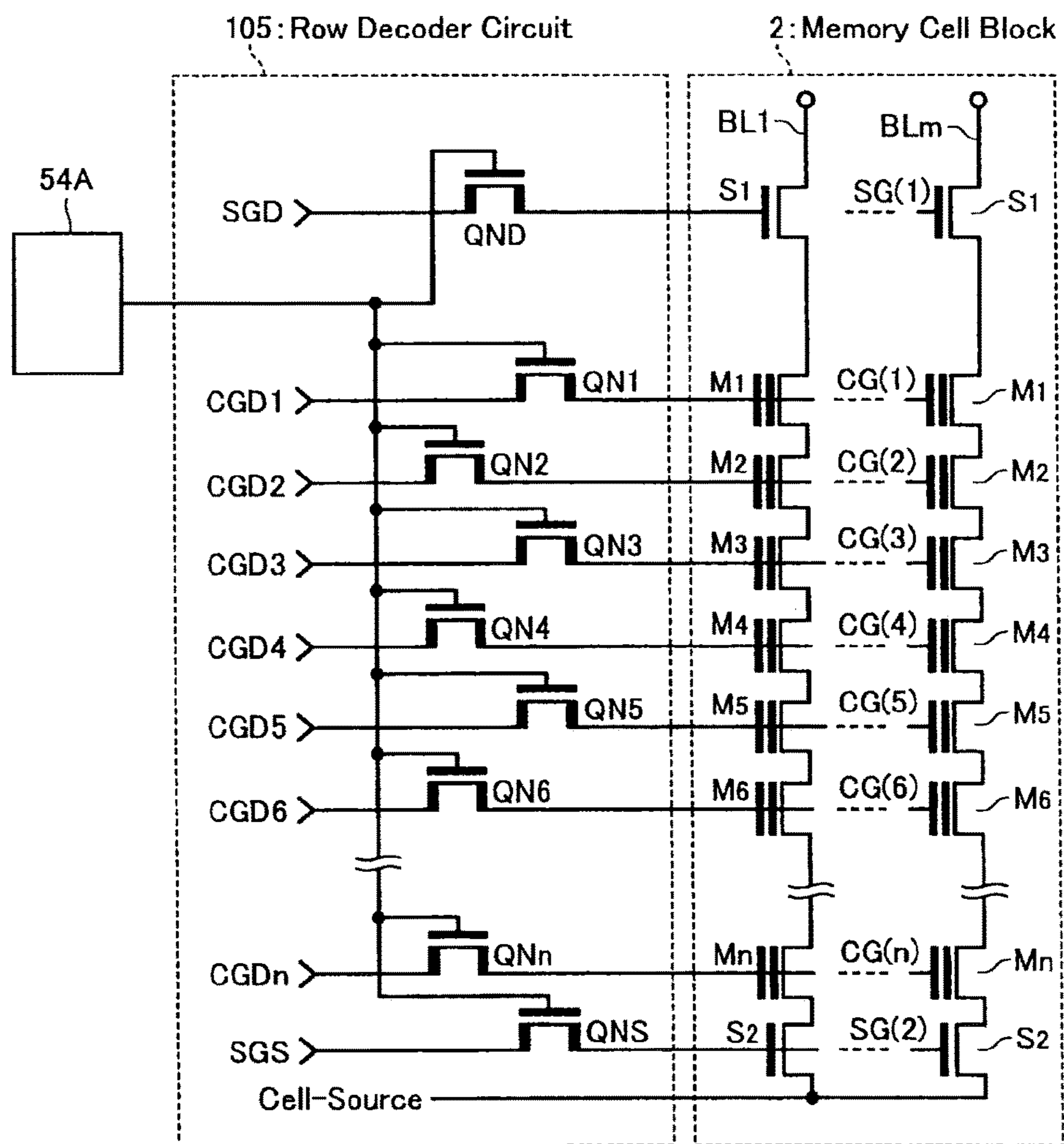


FIG. 6A

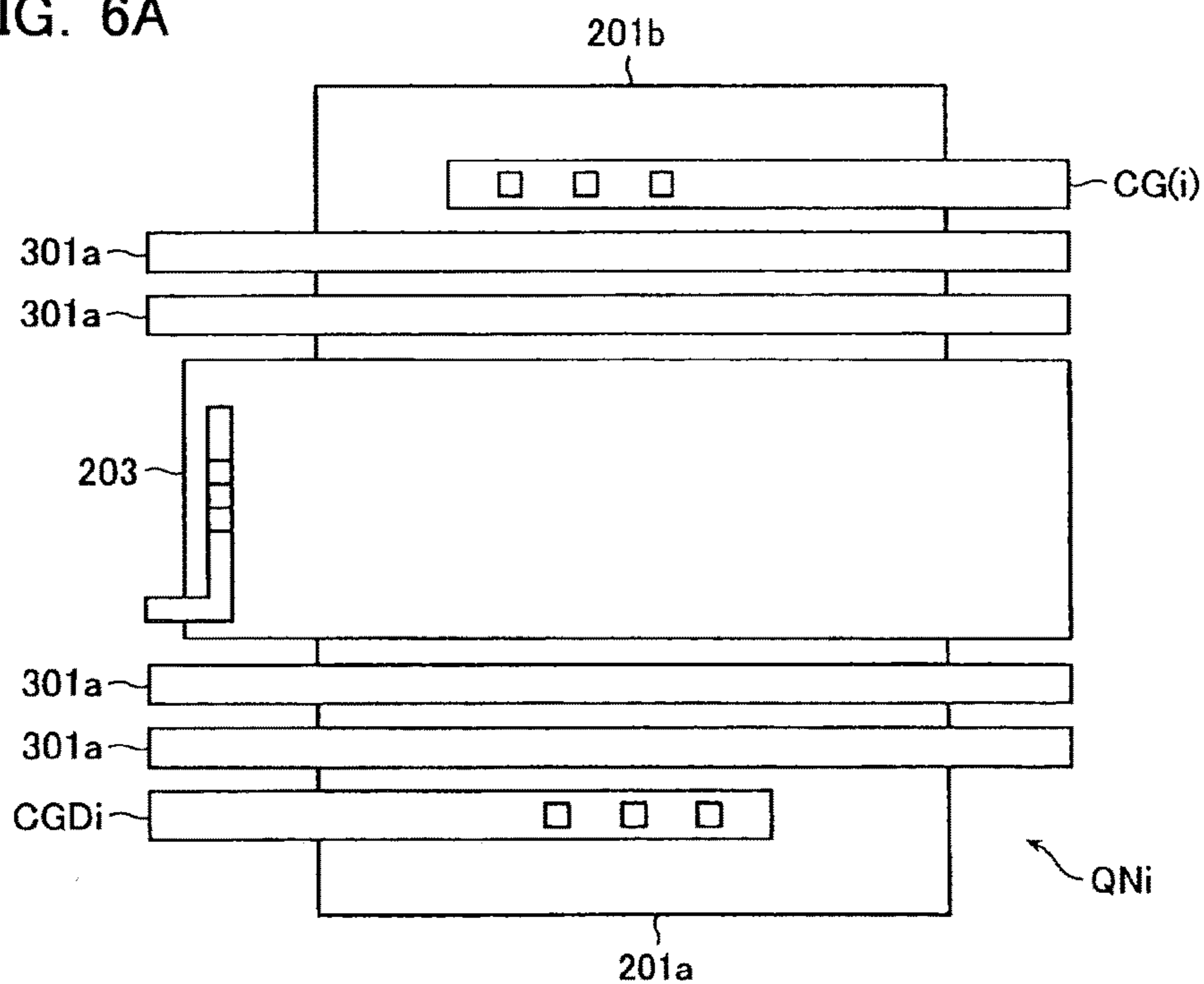


FIG. 6B

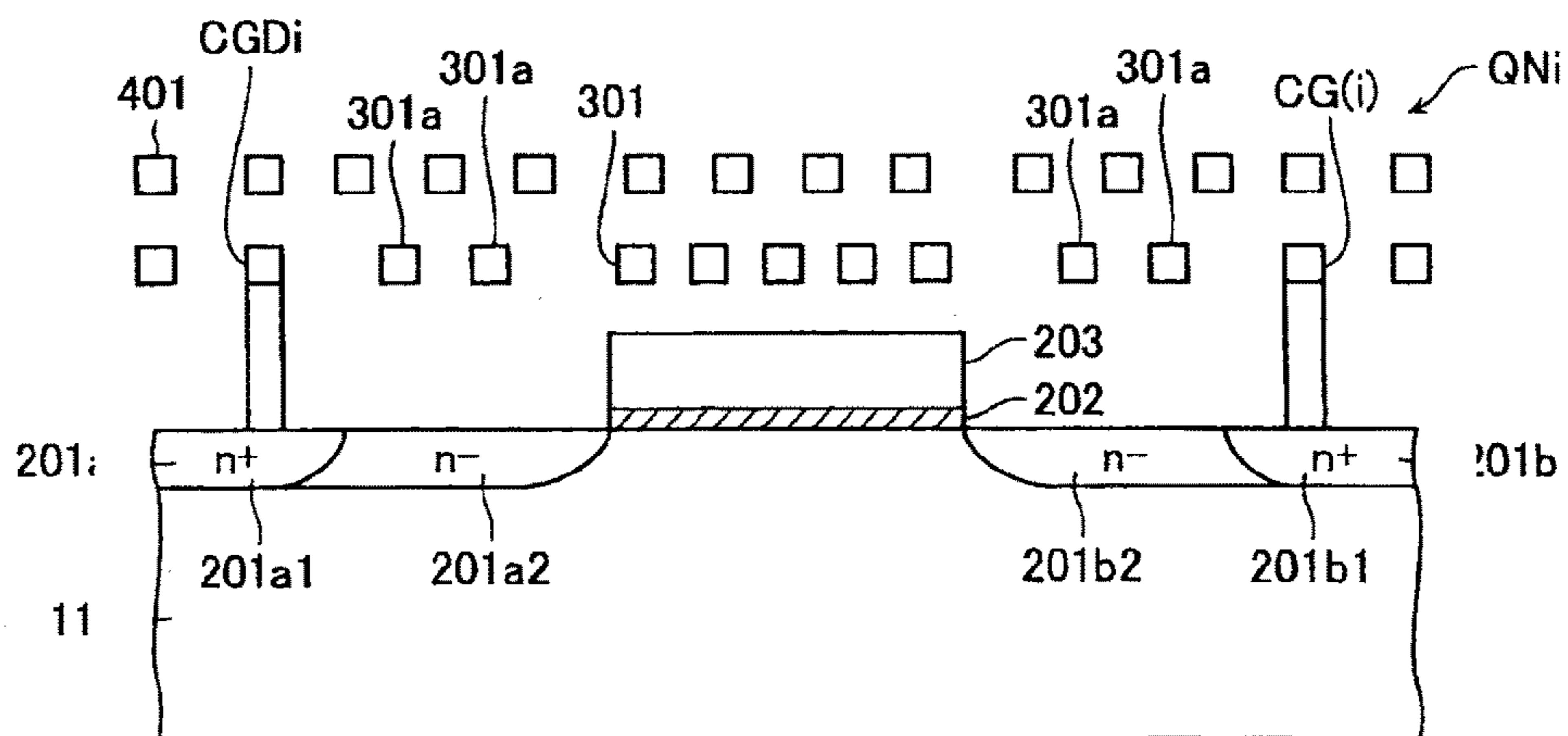




FIG. 7A

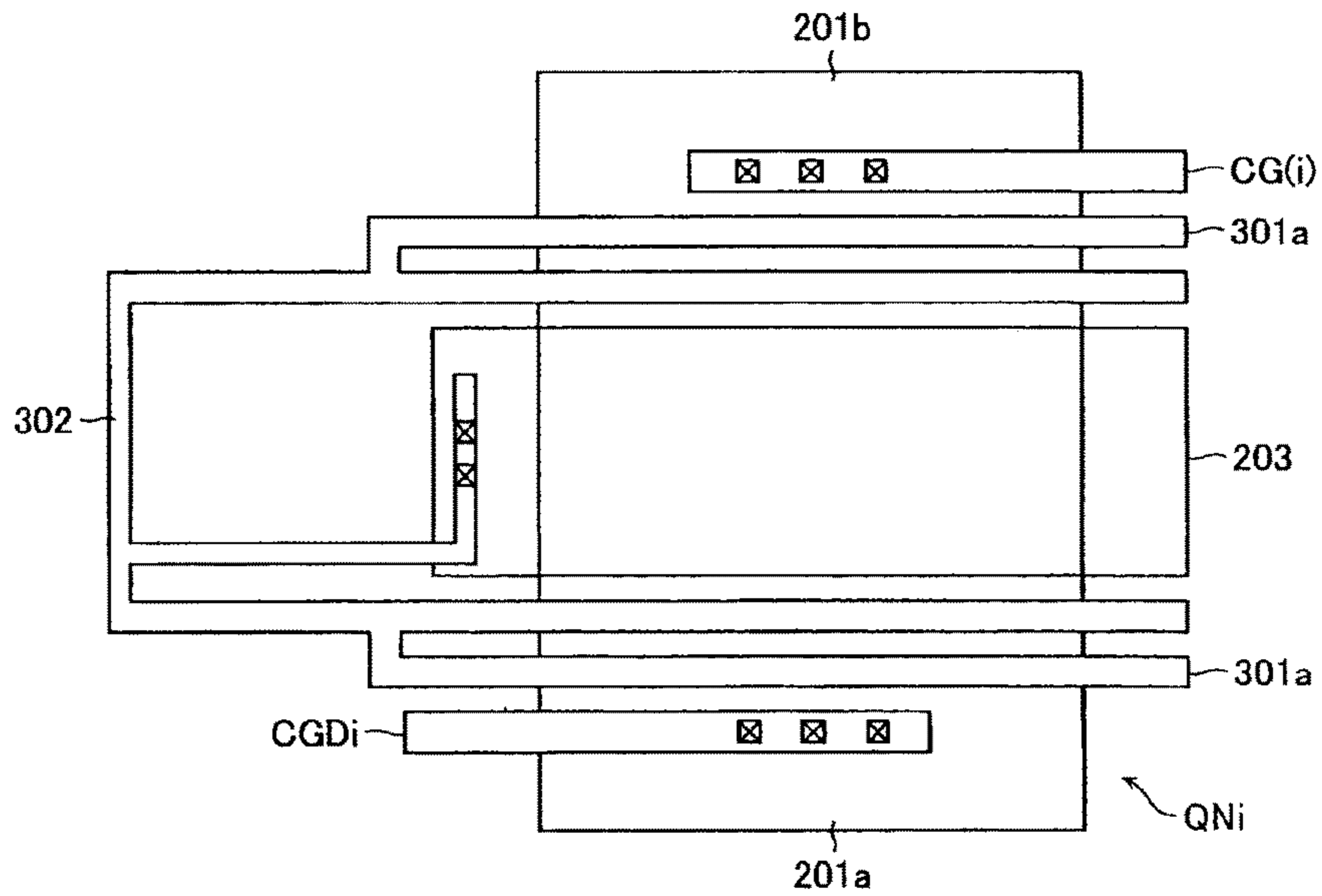


FIG. 7B

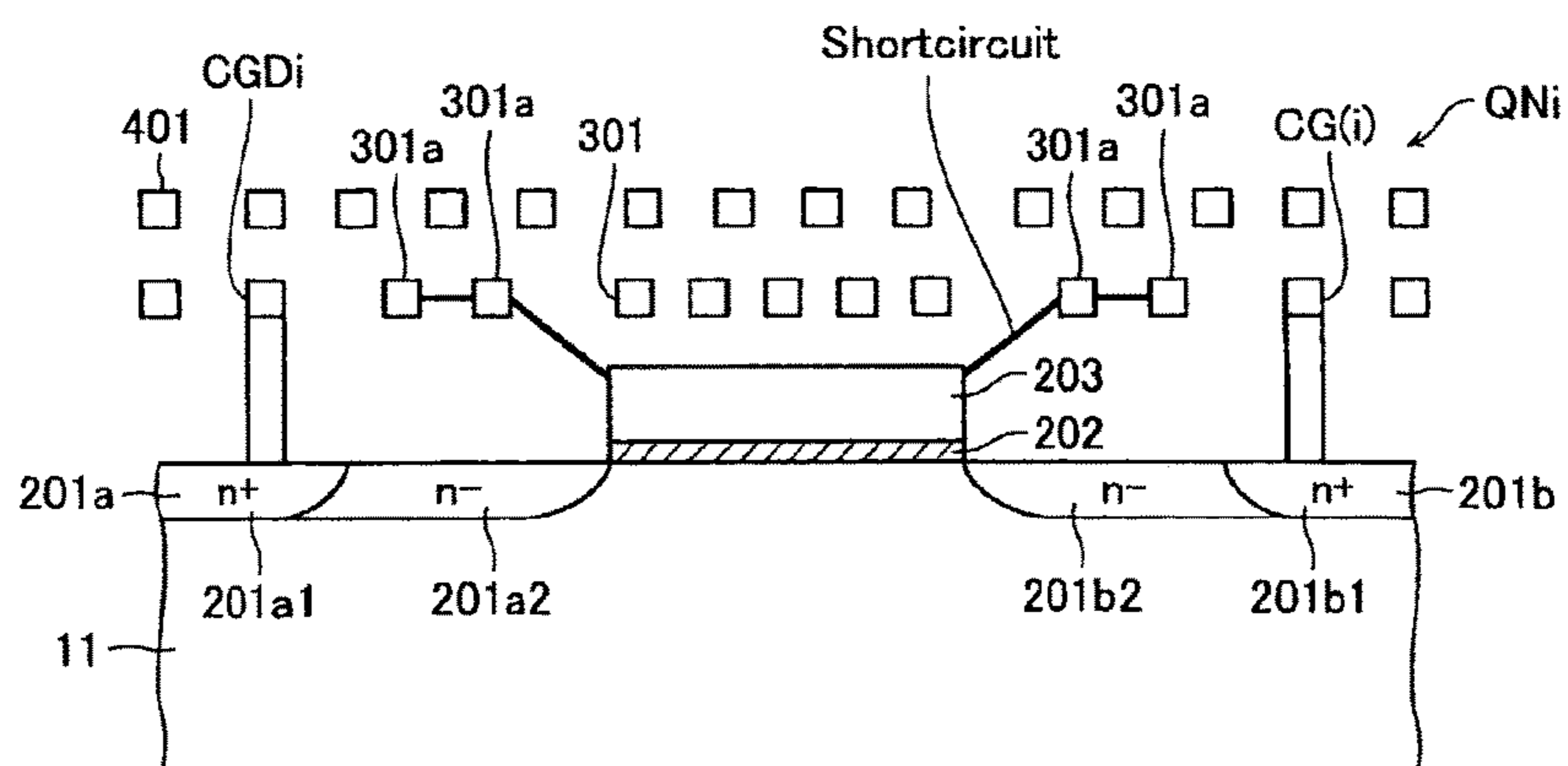


FIG. 8

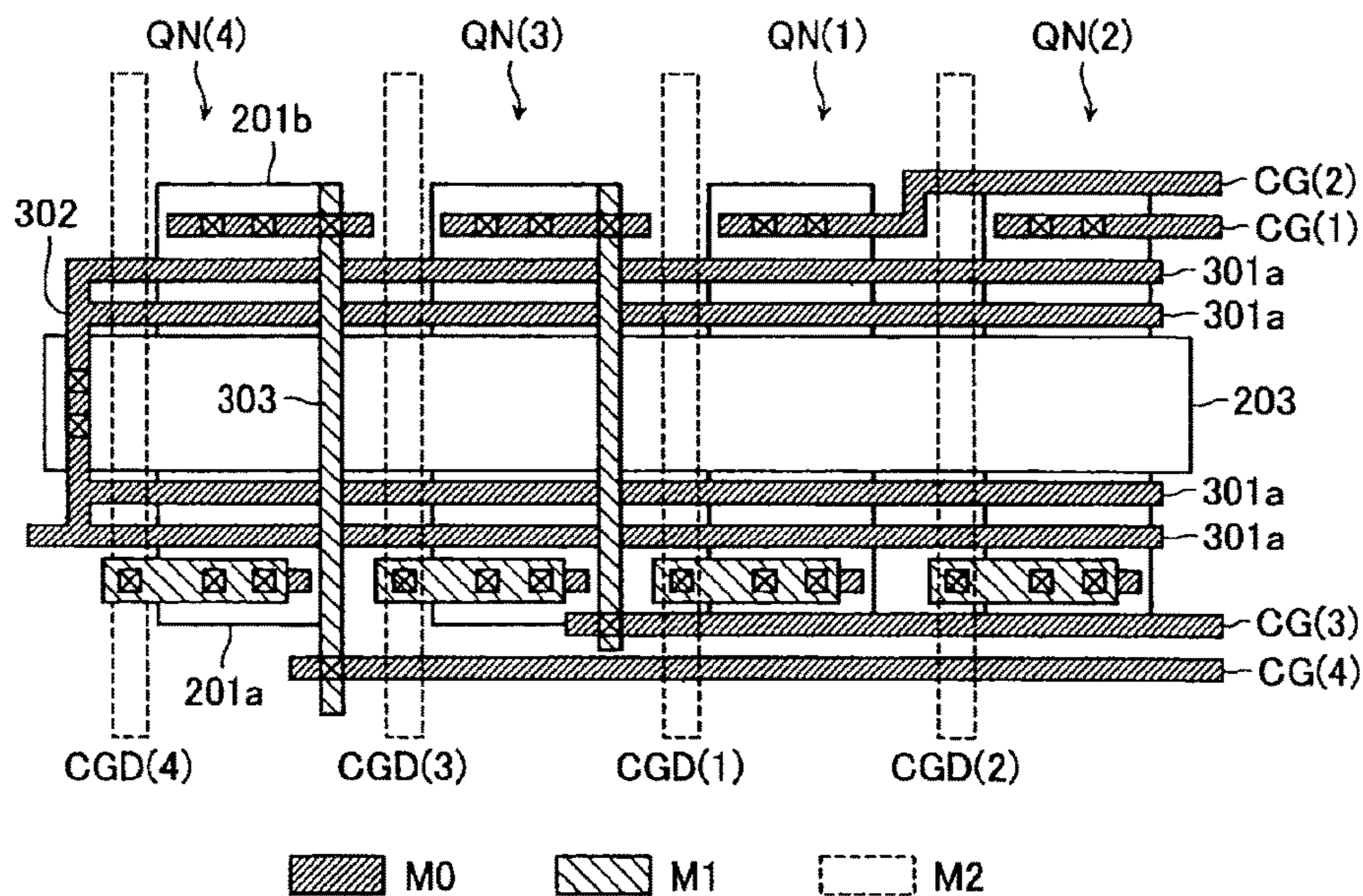


FIG. 9

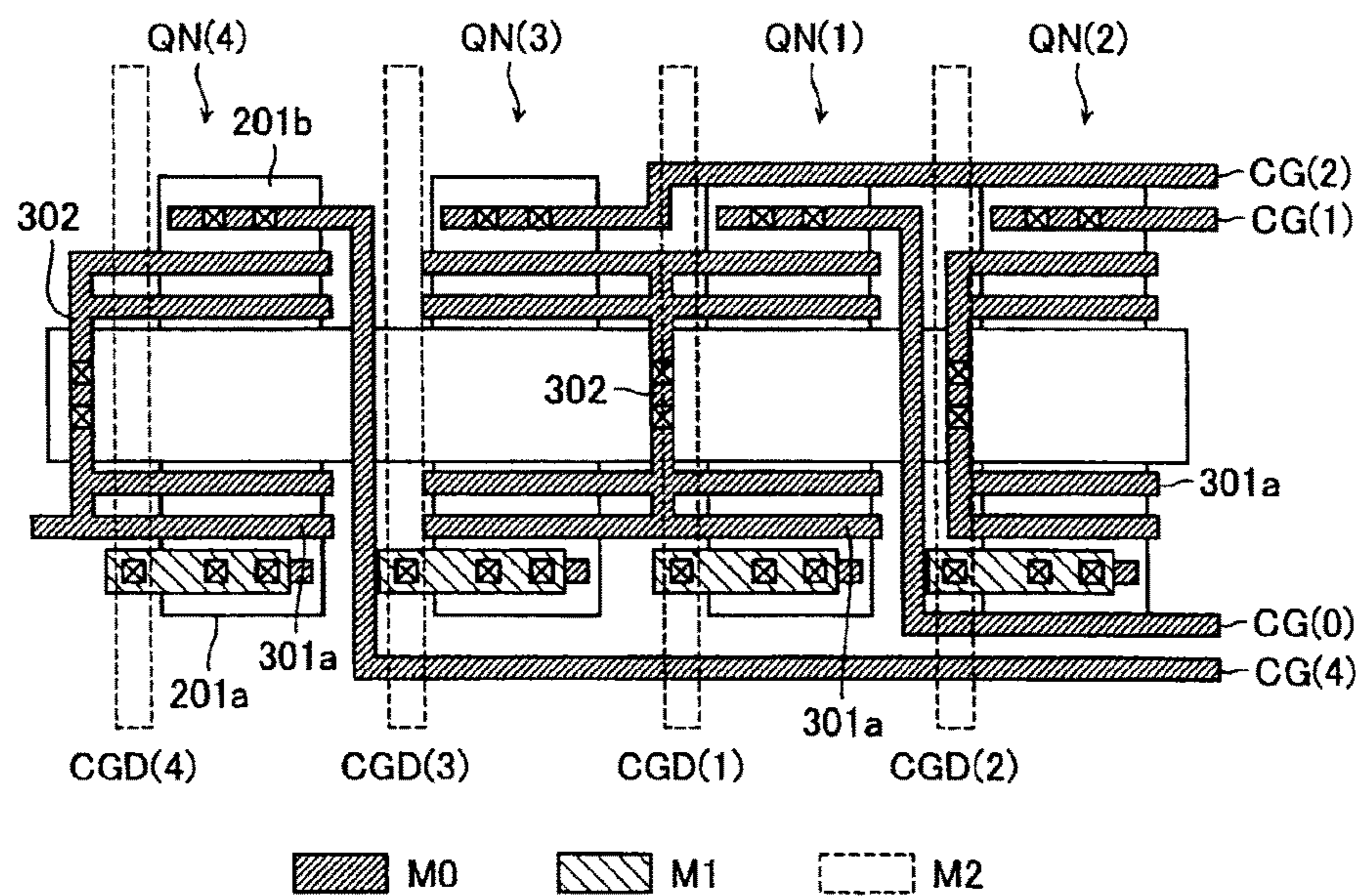


FIG. 10

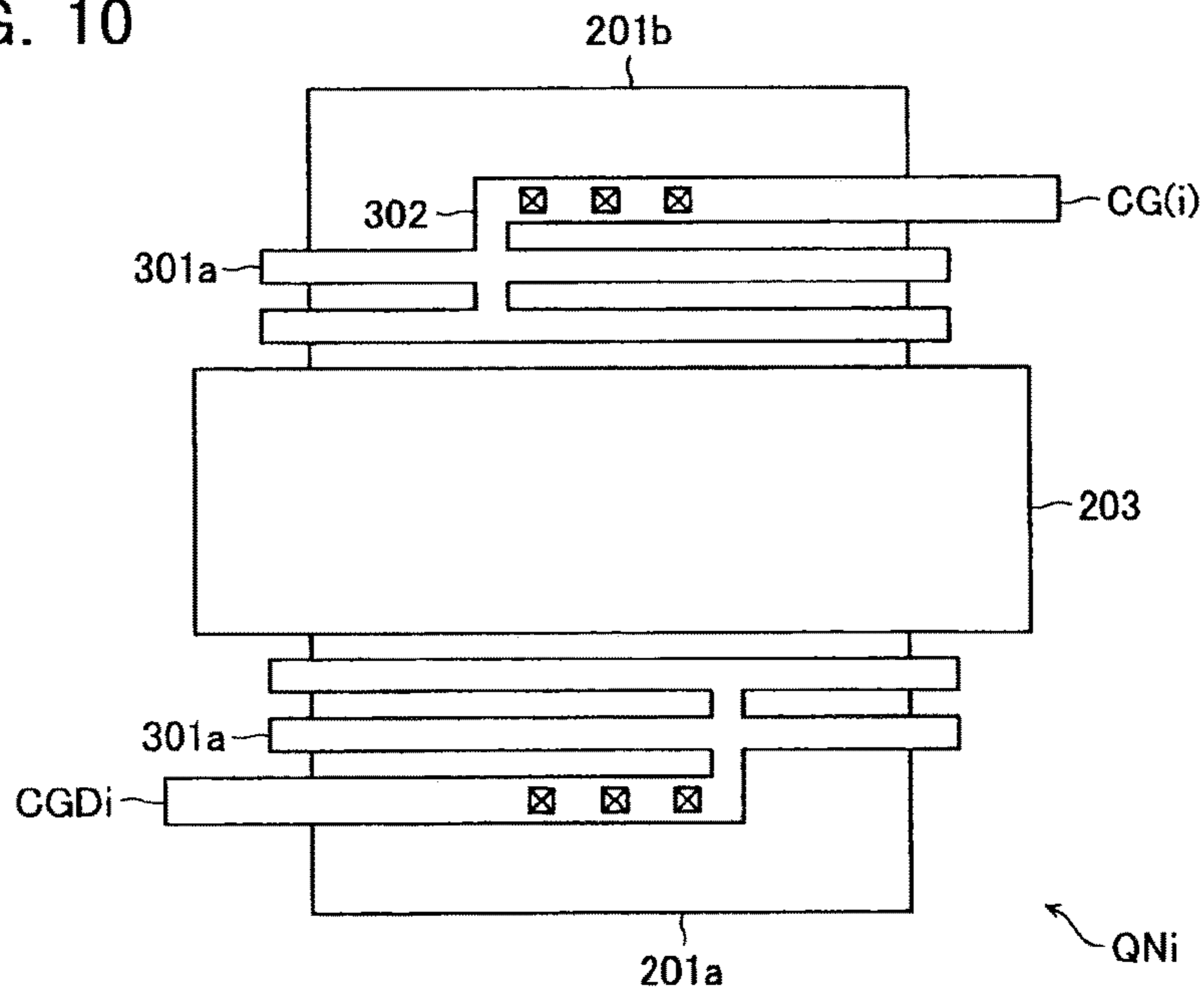


FIG. 11

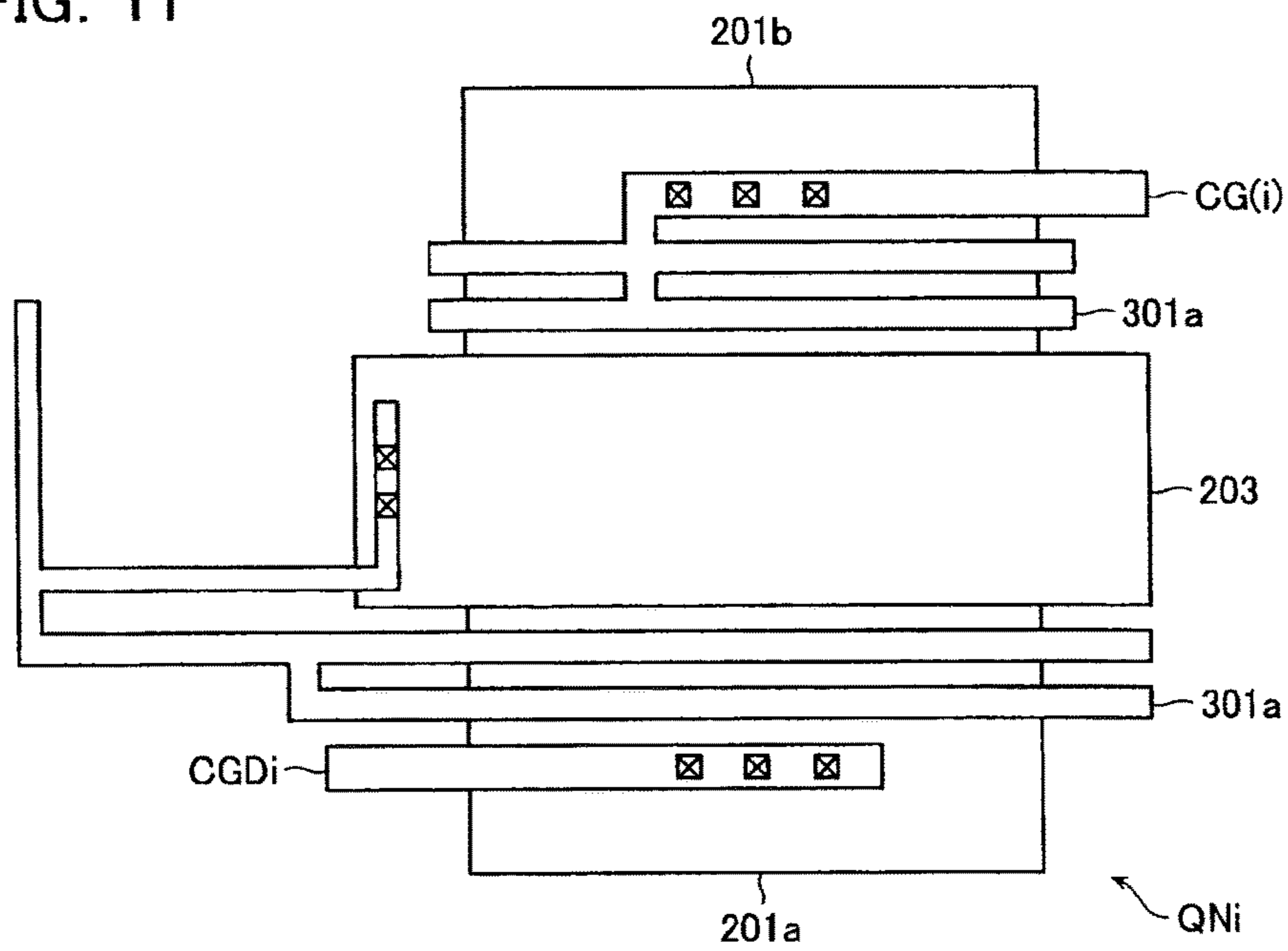
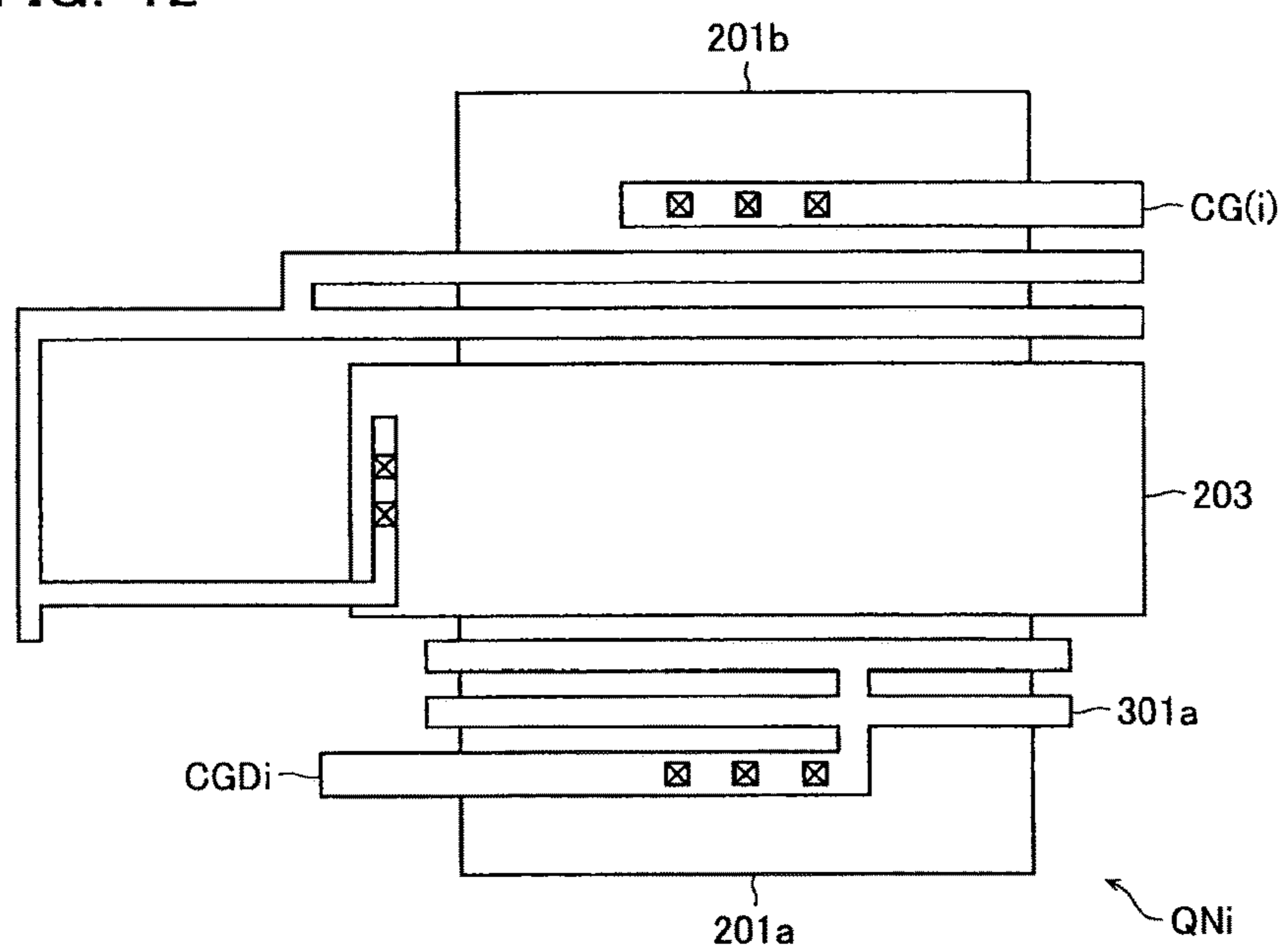


FIG. 12





## NON-VOLATILE SEMICONDUCTOR STORAGE DEVICE

**Matter enclosed in heavy brackets [ ] appears in the original patent but forms no part of this reissue specification; matter printed in italics indicates the additions made by reissue; a claim printed with strikethrough indicates that the claim was canceled, disclaimed, or held invalid by a prior post-patent action or proceeding.**

### CROSS REFERENCE TO RELATED APPLICATIONS

*More than one reissue application has been filed from this patent. The present application is a continuation of reissue application Ser. No. 14/521,160, filed Oct. 22, 2014, which is a continuation of reissue application Ser. No. 13/848,563, filed Mar. 21, 2013.*

This application is based on and claims the benefit of priority from prior Japanese Patent Application No. 2007-328852, filed on Dec. 20, 2007, the entire contents of which are incorporated herein by reference.

### BACKGROUND OF THE INVENTION

#### 1. Field of the Invention

The present invention relates to a non-volatile semiconductor storage device, and, more particularly, a non-volatile semiconductor storage device including transfer transistors to transfer a high voltage.

#### 2. Description of the Related Art

Conventionally, NAND cell type flash memory configures each NAND cell block with a plurality of memory cells connected in series, allowing information to be stored in a non-volatile manner. It has attracted public attention as one of semiconductor storage devices that may achieve high integration. Each memory cell in the NAND cell type flash memory has a FETMOS structure where floating gates (charge accumulation layers) and control gates are laminated on a semiconductor substrate via an insulation film. In addition, there are multiple memory cells connected in series to configure a NAND cell so that a source and a drain are shared between the adjacent ones of the memory cells, which are in turn connected to a corresponding bit line as a unit. Such NAND cells are arranged in a matrix form to configure a memory cell array. The memory cell arrays are integrally formed in a p-type semiconductor substrate or a p-type well area. The drains located at one end of the NAND cells aligned in the column direction of the memory cell array are connected to a bit line via respective selection gate transistors, while the sources located at the other end are also connected to a common source line via respective selection gate transistors. The control gate of each memory transistor and the gate electrode of each selection gate transistor are commonly connected in the row direction of the corresponding memory cell array as a control gate line (word line) and a selection gate line, respectively.

In the NAND cell type flash memory, for example, in writing or erasing data, it is necessary to transfer a voltage higher than the power supply voltage to both the selected control gate line and non-selected control gate lines in the selected block. To transfer such a high voltage to the memory cells, conventional NAND cell type flash memory is provided with a row decoder circuit including transfer transistors with high breakdown voltage (see, for example, Japanese Patent Laid-Open No. 2002-63795). A large num-

ber of transfer transistors are also provided in the peripheral circuitry other than the row decoder to transfer such a high voltage.

The flash memory must be able to transfer a sufficient amount of desired writing potentials, in order to meet the requirements of refinement and multi-level cells (MLC), to make the area of the peripheral circuitry other than the cell arrays as small as possible, and to accommodate multi-value write operations.

However, these transfer transistors with such high breakdown voltage may not transfer a sufficient amount of high voltage to be transferred, which could lead to malfunction, etc.

### SUMMARY OF THE INVENTION

One aspect of the present invention provides a non-volatile semiconductor storage device comprising: a memory cell array having memory cells arranged therein, the memory cells storing data in a non-volatile manner; and a plurality of transfer transistors transferring a voltage to the memory cells, the voltage to be supplied for data read, write and erase operations with respect to the memory cells; each of the plurality of transfer transistors comprising: a gate electrode formed on a semiconductor substrate via a gate insulation film; diffusion layers formed to sandwich the gate electrode therebetween and functioning as drain/source layers; and upper layer wirings provided above the diffusion layers and provided with a predetermined voltage to prevent depletion of the diffusion layers at least when the transfer transistors become conductive.

### BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a block diagram illustrating a general configuration of a NAND cell type flash memory according to a first embodiment of the present invention;

FIG. 2A is a plan view of one part of the NAND cells in the memory cell array **101** of FIG. 1;

FIG. 2B is an equivalent circuit diagram of one part of the NAND cells in the memory cell array **101**;

FIG. 3A is a cross-sectional view taken along line A-A' of FIG. 2A;

FIG. 3B is a cross-sectional view taken along line B-B' of FIG. 2A;

FIG. 4 illustrates an equivalent circuit of the memory cell array **101** having NAND cells arranged therein in a matrix form;

FIG. 5 illustrates an example configuration of the row decoder **105** illustrated in FIG. 1;

FIG. 6A is a plan view of a common transfer transistor QNi;

FIG. 6B is a cross-sectional view of the common transfer transistor QNi;

FIG. 7A is a plan view illustrating a configuration of a transfer transistor QNi according to the first embodiment;

FIG. 7B is a cross-sectional view illustrating a configuration of the transfer transistor QNi according to the first embodiment;

FIG. 8 illustrates an example wiring layout located above a plurality of transfer transistors QNi;

FIG. 9 illustrates an example wiring layout according to a second embodiment of the present invention;

FIG. 10 illustrates an example wiring layout according to a third embodiment of the present invention;

FIG. 11 illustrates a variation of the embodiments of the present invention; and



FIG. 12 illustrates another variation of the embodiments of the present invention.

#### DETAILED DESCRIPTION OF THE EMBODIMENTS

Embodiments of the present invention will now be described below with reference to the accompanying drawings.

##### First Embodiment

FIG. 1 is a block diagram illustrating a general configuration of a NAND cell type flash memory according to a first embodiment of the present invention.

A bit line control circuit (sense amplifier and data latch) **102** is provided for data writing, reading, rewriting and verify reading operations with respect to a memory cell array **101**. The bit line control circuit **102** is connected to a data input/output buffer **106** and receives, as its input, an output from a column decoder **103** that receives an address signal provided by an address buffer **104**.

In addition, a row decoder **105** for controlling control gates and selection gates, and a substrate potential control circuit **107** for controlling the potential of a p-type silicon substrate (or p-type well area) on which the memory cell array **101** is formed are provided with respect to the memory cell array **101**. A voltage generation circuit **120** is also provided as a circuit for generating voltage supplied to the memory cells, etc., that is necessary for writing, reading or the like.

The bit line control circuit **102** mainly comprises CMOS flip-flops to latch data for writing, perform sensing operations for reading the potential of a bit line and for verify reading after a writing operation, and further latch the rewriting data.

FIGS. 2A and 2B are a plan view and an equivalent circuit diagram of one part of the NAND cells in the memory cell array **101**, and FIGS. 3A and 3B are cross-sectional views taken along lines A-A' and B-B' of FIG. 2A. A memory cell array including a plurality of NAND cells is formed on a p-type silicon substrate (or p-type well area) **11** surrounded by a device isolation oxide film **12**. In this embodiment, for example, focusing on one NAND cell,  $n$  memory cells  $M1-Mn$  are connected in series to configure one NAND cell.

Each of the memory cells  $M1-Mn$  is configured in such a way that a floating gate **14** ( $14_1, 14_2, \dots, 14_n$ ) is formed on the substrate **11** via a gate insulation film **13**, on which a control gate **16** (=word lines:  $16_1, 16_2, \dots, 16_n$ ) is further formed via an insulation film **15**. N-type diffusion layers **19** corresponding to the sources and drains of these memory cells are connected so as to be shared by the adjacent ones, by which the memory cells are connected in series.

Selection gates **14D, 16D, and 14S, 16S** are formed on the drain side and the source side of the NAND cell. These selection gates **14D, 16D, and 14S, 16S** are formed at the same time as the floating gates **14** and control gates **16** of the memory cells. These selection gates configures selection transistors **S1** and **S2**.

The substrate **11** with the so-formed elements is covered with an insulation film **17**, on which a bit line **18** is disposed. The bit line **18** is connected to those drain-side diffusion layers **19** located on one end of the NAND cell. The control gates **16** of the NAND cell that are aligned in the row direction are commonly disposed as control gate lines  $CG(1), CG(2), \dots, CG(n)$ . These control gates represent word lines. The selection gates **14D, 16D, and 14S, 16S** are

also disposed in the column direction in a continuous manner as selection gate lines  $SG(1)$  and  $SG(2)$ , respectively.

FIG. 4 illustrates an equivalent circuit of the memory cell array **101** having such NAND cells arranged therein in a matrix form. A group of NAND cells that shares the same word lines and the same selection gate lines, indicated by an area illustrated by the dotted line of FIG. 4, is referred to as "one block". In normal reading and writing operations, only one of multiple blocks is selected (which is, hereinafter, referred to as the "selected block").

FIG. 5 illustrates an example configuration of the row decoder **105**. In the case of FIG. 5, a row decoder circuit that configures the row decoder **105** is positioned at one end of a memory cell block **2** in the memory cell array **101**. The row decoder circuit **105** comprises transfer transistors  $QN0-QNn$ ,  $QND$ , and  $QNS$  that are connected to the control gate lines  $CG(1)-CG(n)$  and the selection gate lines  $SG(1)$  and  $SG(2)$ , respectively. In addition, each one of the transfer transistors  $QN1-QNn$  is connected to the respective one of the control gate lines  $CG(1)-CG(n)$ .

That is, a current path for respective one of the transfer transistors  $QN1-QNn$  is connected between each one of the control gate lines  $CG(1)-CG(n)$  and each one of signal input nodes  $CGD1-CGDn$ . In addition, the current path of the transfer transistor  $QND$  is connected between the selection gate line  $SG(1)$  and its signal input node  $SGD$ . Further, the current path of the transfer transistor  $QNS$  is connected between the selection gate line  $SG(2)$  and its signal input node  $SGS$ . A voltage switching circuit **54A** is also provided for setting the gate voltages of the transfer transistors  $QN0-QNn$ ,  $QND$ , and  $QNS$  to switch the voltages of the control gate lines  $CG(1)-(n)$ , the selection gate line  $SG(1)$  and  $SG(2)$ . Besides, it is herein assumed that all of the transfer transistors  $QN0-QNn$ ,  $QND$ , and  $QNS$  represent enhancement-type n-type MOS transistors.

As described above, the row decoder circuit **105** comprises the transfer transistors  $QN0-QNn$ ,  $QND$ , and  $QNS$  for transferring a high voltage such as a writing voltage (not less than 20V) to a word line  $WL$ , the selection gate lines  $SG(1)$  and  $SG(2)$ . Such transistors for transferring a high voltage are provided not only in the row decoder circuit **105**, but, for example, in the above-mentioned substrate potential control circuit **107** or the voltage switching circuit **54A**.

When transferring a high voltage  $VD$  from a drain-side node (in the case of n-channel type MOSFET) using these transfer transistors  $QN0-QNn$ ,  $QND$ , and  $QNS$ , the voltage  $VD$  plus a threshold voltage  $V_{th}$  ( $VD+V_{th}$ ) is applied to the corresponding gate electrode. As a result, the potential on the source side of the transistors becomes a desired potential  $VD$ .

FIGS. 6A and 6B are a plan view and a cross-sectional view of a common transfer transistor  $QNi$  (hereinafter,  $i=1$  to  $n$ ). A transfer transistor  $QNi$  comprises an n-type drain diffusion area **201a** and a source diffusion area **201b** on the p-type silicon substrate **11**. Note that the drain diffusion area **201a** has a high concentration area **201a1** and an LDD area **201a2** with a lower impurity concentration than the high concentration area **201a1**. Similarly, the source diffusion area **201b** has a high concentration area **201b1** and an LDD area **201b2** with a lower impurity concentration than the high concentration area **201b1**.

A signal input node  $CGDi$  is connected to the drain diffusion area **201a** via a contact, while a control gate line  $CG(i)$  is connected to the source diffusion area **201b**. A gate



electrode **203** is formed at a position between the drain diffusion area **201a** and the source diffusion area **201b** via a gate insulation film **202**.

There are many wirings **301** disposed on the transfer transistor QNi that are independent of the transfer transistor QNi. Examples of the wirings **301** include lead wirings of a control gate CG(i), etc. These wirings **301** could have a negative impact on the operation of the transfer transistor QNi depending on the magnitude of the applied voltage. Particularly, if the voltage applied to those wirings **301** running above the drain diffusion area **201a** and the source diffusion area **201b** is smaller (e.g., 0V) than the high voltage transferred by the transfer transistor QNi, then a sufficient amount of voltage cannot be transferred, which could cause malfunction in the flash memory.

That is, when a predetermined gate voltage ( $VD+V_{th}$ ) is provided to the gate electrode **203** of the transfer transistor QNi, then a high voltage  $VD$  is supplied from the drain and transferred to the source side, the drain diffusion area **201a** and the source diffusion area **201b** are depleted due to the wiring **301a** to which 0V has been applied. This may lead to an increase in respective resistance of the drain diffusion area **201a** and the source diffusion area **201b** such that a desired voltage  $VD$  cannot be transferred to the source side. Particularly, a sufficient margin cannot be obtained when writing multi-value data to one memory cell MC.

To address this problem, a method is also applicable to provide the wirings **301** by bypassing above the drain diffusion area **201a** and the source diffusion area **201b**. However, if there exists an additional low-potential wiring on the upper layer, the effects, as mentioned above, due to this wiring are not negligible.

FIGS. 7A and 7B are a plan view and a cross-sectional view illustrating a configuration of a transfer transistor QNi according to the first embodiment. In this embodiment, those wirings **301a** that are located above the drain diffusion area **201a** and the source diffusion area **201b** (in particular, the LDD areas **201a2** and **201b2**) are short-circuited to the gate electrode **203** through a short-circuit wiring **302**, thereby providing dummy wirings (in the case of FIGS. 7A and 7B, dummy wirings are only formed above the LDD areas **201a2** and **201b2**). Thus, when a predetermined gate voltage is supplied to the gate electrode **203**, the same voltage is also supplied to the wirings **301a**. This may prevent depletion of the drain diffusion area **201a** and the source diffusion area **201b** in transferring a high voltage by the transfer transistor QNi and allow the high voltage to be transferred successfully. In addition, upon formation of the wirings **301a** being short-circuited to the gate electrode **203**, the wirings **301** function as shielding wires for the wirings on the upper layer. Accordingly, an improved degree of freedom may be provided for the wiring layout of the wirings on the upper layer.

Note that it is preferable to allow a sufficient distance between the wirings **301a** short-circuited to the gate electrode **203** and the other wirings to prevent an increase in parasitic capacitance due to the coupling.

FIG. 8 illustrates an example wiring layout located above a plurality of transfer transistors QNi. The transfer transistors QNi share one gate electrode **203**. In FIG. 8, each wiring includes M0 wirings on the bottom layer, M1 wirings on the upper layer, and further M2 wirings on the top of the upper layer.

The above-mentioned wirings **301a** and the short-circuit wiring **302** are configured by the M0 wirings on the bottom layer. The short-circuit wiring **302** is electrically connected to the gate electrode **203** via a contact. The wirings **301a**

which represent dummy wirings are formed across the plurality of transfer transistors QNi and connected to the short-circuit wiring **302** at one position so that a voltage is supplied thereto by the gate electrode **203**.

The signal input node CGDi is connected to the drain diffusion area **201a** of each transfer transistor QNi and configured by three layers of the M0, M1 and M2 wirings. In addition, the control gate lines CG(0) and CG(1) are drawn by connecting the M0 wirings to the source diffusion area **201b** via a contact. The control gate lines CG(2) and CG(3) are drawn by connecting M0 wirings to M1 wirings **303** via a contact and further connecting the M1 wirings **303** to other M1 wirings.

Note that, in this embodiment, the wirings **301a** are provided that are supplied with a predetermined voltage when a predetermined gate voltage is supplied to the gate of the transfer transistor QNi (FIG. 7A). However, the configuration as illustrated in FIG. 7A is useful when the transfer transistor QNi is an enhancement-type n-type MOS transistor. If the transfer transistor QNi is a depression-type n-channel type MOS transistor, then the configuration as illustrated in FIG. 6A might be preferable rather than that illustrated in FIG. 7A. That is, as illustrated in FIG. 6A, it might be preferable for the depression-type to provide those wirings **301a** where a fixed voltage smaller than the gate voltage, e.g., 0V is applied on the diffusion layers **201a** and **201b**. This is for the following reasons:

The depression-type MOS transistors have higher impurity concentration in their channels in which large current flows than that of the enhancement-type. In addition, a surface breakdown voltage is required to cut off the high voltage. To this extent, the depression-type MOS transistors provide a lower surface breakdown voltage than the enhancement-type MOS transistors due to the higher impurity concentration involved in their channels. Thus, it is preferable that a voltage of, e.g., 0V, that is lower than the voltage applied to the gate electrode **203** is always applied to those wirings **301a** that are disposed on the diffusion layers **201a** and **201b** of the depression-type MOS transistors. Consequently, a higher diffusion-layer resistance may be provided in the diffusion layers **201a** and **201b**, thereby improving the surface breakdown voltage. In addition to this, further improvements may be achieved if those wirings (in particular, the M0 wirings) to which the high voltage is applied are not positioned adjacent the diffusion layers **201a** and **201b**.

If there are both enhancement-type n-type MOS transistors and depression-type n-type MOS transistors in one memory chip as transfer transistors, it is preferable for the latter to employ the wiring layout as illustrated in FIG. 6A and for the former the wiring layout as illustrated in FIG. 7A, as needed.

#### Second Embodiment

Referring now to FIG. 9, a second embodiment of the present invention will be described below. The second embodiment is different from the first embodiment in the wiring layout with respect to the transfer transistors QNi, while other features are the same as the first embodiment.

FIG. 9 is a plan view illustrating the wiring layout of the transfer transistors QNi provided in a non-volatile semiconductor storage device according to the second embodiment of the present invention. Besides, in FIG. 9, the same reference numerals represent the same components as the first embodiment and detailed description thereof will be omitted.



Note that this embodiment also has a preferable configuration to be applied to the enhancement-type MOS transistors. On the other hand, as with the first embodiment, it is often preferable for the depression-type MOS transistors to apply the configuration of FIG. 6A.

Further, if there is a mix of enhancement-type n-type MOS transistors and depression-type n-type MOS transistors in one memory chip as transfer transistors, it is preferable for the latter to employ the wiring layout as illustrated in FIG. 6A and for the former the wiring layout as illustrated in FIG. 9, as needed.

In this embodiment, the wirings 301a are arranged separately for each one or two transfer transistors QNi rather than being disposed common to the plurality of transfer transistors QNi. In addition, each separate wiring 301a is short-circuited to the gate electrode 203 through the short-circuit wiring 302. As can be seen, since the wirings 301a are separated in any suitable manner, other wirings may be formed at those portions resulting from the separation and hence providing an improved degree of freedom for the wiring layout.

### Third Embodiment

Referring now to FIG. 10, a third embodiment of the present invention will be described below. The third embodiment is different from the first embodiment in the wiring layout with respect to the transfer transistors QNi, while other features are the same as the first embodiment.

FIG. 10 is a plan view illustrating the wiring layout of the transfer transistors QNi provided in a non-volatile semiconductor storage device according to the third embodiment of the present invention. Besides, in FIG. 10, the same reference numerals represent the same components as the first embodiment and detailed description thereof will be omitted. Note that this embodiment also has a preferable configuration to be applied to the enhancement-type MOS transistors. On the other hand, as with the first embodiment, it is often preferable for the depression-type MOS transistors to apply the configuration of FIG. 6A, as needed. If there is a mix of enhancement-type n-type MOS transistors and depression-type n-type MOS transistors in one memory chip as transfer transistors, it is preferable for the latter to employ the wiring layout as illustrated in FIG. 6A and for the former the wiring layout as illustrated in FIG. 10, as needed.

In this embodiment, as illustrated in FIG. 10, the wirings 301a which represent dummy wirings are not connected to the gate electrode 203, but instead to a control gate line CG(i) or a signal input node CGDi via a short-circuit wiring 302. Also with this configuration, it is possible to prevent depletion of the diffusion areas 201a and 201b when the transfer transistors QNi are conductive, which may provide the same advantages as the above-mentioned embodiments.

While embodiments of the present invention have been described, the present invention is not intended to be limited to the disclosed embodiments and various other changes, additions or the like may be made thereto without departing from the spirit of the invention. For example, the above embodiments have been described with reference to the transfer transistors in the row decoder, the present invention is not limited to the disclosed embodiments and it is applicable to any transfer transistors that transfer a high voltage. The above embodiments may also be combined in any suitable manner. For example, as illustrated in FIG. 11, those wirings 301a on the drain diffusion area 201a may be short-circuited to the gate electrode 203, while those on the source diffusion area 201b may be short-circuited to the

control gate lines CG(i). Conversely, as illustrated in FIG. 12, those wirings 301a on the drain diffusion area 201a may be short-circuited to the signal input nodes CGDi, while those on the source diffusion area 201b may be short-circuited to the gate electrode 203.

What is claimed is:

**[1.** A non-volatile semiconductor storage device comprising:

a memory cell array having memory cells arranged therein, the memory cells storing data in a non-volatile manner; and

a plurality of transfer transistors transferring a voltage to the memory cells, the voltage to be supplied for data read, write and erase operations with respect to the memory cells;

each of the plurality of transfer transistors comprising:

a gate electrode formed on a semiconductor substrate via a gate insulation film;

diffusion layers formed to sandwich the gate electrode therebetween and functioning as drain/source layers; and

upper layer wirings provided above the diffusion layers, wherein

the transfer transistors comprise enhancement-type transistors and depression-type transistors,

the upper layer wirings provided above the transfer transistors corresponding to the enhancement-type transistors are provided with a predetermined voltage at least when the transfer transistors become conductive to prevent depletion of the diffusion layer, and

the upper layer wirings provided above the transfer transistors corresponding to the depression-type transistors are supplied with a fixed voltage smaller than a voltage applied to their gates.]

**[2.** The non-volatile semiconductor storage device according to claim 1, further comprising:

a row decoder selecting a word line provided above the memory cell array,

wherein the transfer transistors are included in the row decoder.]

**[3.** The non-volatile semiconductor storage device according to claim 1, wherein

the upper layer wirings of the transfer transistors corresponding to the enhancement-type transistors are provided with the same voltage as that of the gate electrode.]

**[4.** The non-volatile semiconductor storage device according to claim 3, wherein

the upper layer wirings of the transfer transistors corresponding to the enhancement-type transistors are short-circuited to the gate electrode.]

**[5.** The non-volatile semiconductor storage device according to claim 1, wherein

the upper layer wirings of the transfer transistors corresponding to the enhancement-type transistors are provided with the same voltage as that of the diffusion layers.]

**[6.** The non-volatile semiconductor storage device according to claim 5, wherein

the upper layer wirings of the transfer transistors corresponding to the enhancement-type transistors are short-circuited to the diffusion layers.]

**[7.** The non-volatile semiconductor storage device according to claim 1, further comprising:

a short-circuit wiring short-circuiting the upper layer wirings to the gate electrode.]



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**[8.** The non-volatile semiconductor storage device according to claim 1, wherein

the memory cell array comprises NAND cells including a plurality of serially-connected memory cells, and selection transistors connected to the NAND cells.]

**[9.** The non-volatile semiconductor storage device according to claim 1, wherein

each of the diffusion layers comprises a high concentration area with a first impurity concentration and an LDD area with a second impurity concentration lower than the first impurity concentration.]

**[10.** The non-volatile semiconductor storage device according to claim 9, wherein

the upper layer wirings are provided above the LDD areas.]

**[11.** The non-volatile semiconductor storage device according to claim 1, wherein

the plurality of transfer transistors share the gate electrode as well as the upper layer wirings that are disposed in a continuous manner.]

**[12.** The non-volatile semiconductor storage device according to claim 1, wherein

the plurality of transfer transistors share the gate electrode, and

the upper layer wirings are separately disposed for one or two of the plurality of transfer transistors.]

**[13.** The non-volatile semiconductor storage device according to claim 1, further comprising:

a signal line electrically connected to the diffusion layers, wherein the upper layer wirings are short-circuited to the signal line.]

**[14.** A non-volatile semiconductor storage device comprising:

a memory cell array having memory cells arranged therein, the memory cells storing data in a non-volatile manner; and

a plurality of transfer transistors transferring a voltage to the memory cells, the voltage to be supplied for data read, write and erase operations with respect to the memory cells;

each of the plurality of transfer transistors comprising: a gate electrode formed on a semiconductor substrate via a gate insulation film;

diffusion layers formed to sandwich the gate electrode therebetween and functioning as drain/source layers; and

upper layer wirings provided above the diffusion layers, wherein

the transfer transistors comprise enhancement-type transistors and depression-type transistors,

the upper layer wirings provided above the transfer transistors corresponding to the enhancement-type transistors are provided with the same voltage as applied to the diffusion layers or the gate voltage at least when the transfer transistors become conductive, and

the upper layer wirings provided above the transfer transistors corresponding to the depression-type transistors are supplied with a fixed voltage smaller than a voltage applied to their gates.]

**[15.** The non-volatile semiconductor storage device according to claim 14, further comprising:

a row decoder selecting a word line provided above the memory cell array,

wherein the transfer transistors are included in the row decoder.]

**[16.** The non-volatile semiconductor storage device according to claim 14, wherein

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the upper layer wirings of the transfer transistors corresponding to the enhancement-type transistors are short-circuited to the gate electrode.]

**[17.** The non-volatile semiconductor storage device according to claim 14, wherein

the upper layer wirings of the transfer transistors corresponding to the enhancement-type transistors are short-circuited to the diffusion layers.]

**[18.** A non-volatile semiconductor storage device comprising:

a memory cell array having memory cells arranged therein, the memory cells storing data in a non-volatile manner; and

a plurality of transfer transistors transferring a voltage to the memory cells, the voltage to be supplied for data read, write and erase operations with respect to the memory cells;

each of the plurality of transfer transistors comprising:

a gate electrode formed on a semiconductor substrate via a gate insulation film;

diffusion layers formed to sandwich the gate electrode therebetween and functioning as drain/source layers; and

upper layer wirings provided above the diffusion layers and provided with a predetermined voltage to prevent depletion of the diffusion layers at least when the transfer transistors become conductive,

wherein the plurality of transfer transistors share the gate electrode, and

the upper layer wirings are separately disposed for one or two of the plurality of transfer transistors.]

*19. A non-volatile semiconductor storage device comprising:*

*a memory cell array including a plurality of memory cells;*

*a plurality of transfer transistors configured to transfer a voltage to the memory cells, the transfer transistors including a first transfer transistor and a second transfer transistor, the first transfer transistor comprising first drain/source regions, the second transfer transistor comprising second drain/source regions, the first and second transfer transistors comprising a common gate electrode extending in a first direction; and*

*wirings provided above the first drain/source regions and the second drain/source regions, the wirings including a first wiring, the first wiring comprising a first portion, a second portion, and a third portion each provided above one of the first drain/source regions, the first portion and the third portion extending in the first direction, the second portion extending in a second direction crossing the first direction, the first portion being connected to the one of the first drain/source regions via a first contact, and the second portion and the third portion being provided between the first portion and the common gate electrode, the second portion being connected to the first portion and the third portion.*

*20. The non-volatile semiconductor storage device according to claim 19, wherein*

*the first wiring connects to gates of the memory cells.*

*21. The non-volatile semiconductor storage device according to claim 19, further comprising a row decoder selecting a word line provided above the memory cell array, wherein*

*the first and second transfer transistors are included in the row decoder.*



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22. *The non-volatile semiconductor storage device according to claim 19, wherein*

*the first wiring further comprises a fourth portion extending in the first direction and connected to the second portion.*

23. *The non-volatile semiconductor storage device according to claim 19, wherein*

*both the first portion and the second portion are arranged in a same layer.*

24. *The non-volatile semiconductor storage device according to claim 19, wherein*

*the wirings includes a second wiring, a third wiring and a fourth wiring,*

*the second wiring comprises a fourth portion extending in the first direction and connected to another one of the first drain/source regions via a second contact, and the third wiring and the fourth wiring are provided between the fourth portion and the common gate electrode.*

25. *The non-volatile semiconductor storage device according to claim 24, wherein*

*the second wiring connects to gates of the memory cells.*

26. *The non-volatile semiconductor storage device according to claim 24, wherein*

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*both the first wiring and the second wiring are arranged in a same layer.*

27. *The non-volatile semiconductor storage device according to claim 19, wherein*

5 *the wirings includes a fifth wiring comprising a fifth portion, a sixth portion, and a seventh portion each provided above one of the second drain/source regions, the fifth portion and seventh portion extending in the first direction, the sixth portion extending in the second direction, the fifth portion being connected to the one of the second drain/source regions via a third contact, and the sixth portion and the seventh portion being provided between the fifth portion and the common gate electrode, the sixth portion being connected to the fifth portion and the seventh portion.*

28. *The non-volatile semiconductor storage device according to claim 24, wherein the wirings includes a sixth wiring,*

*the sixth wiring includes an eighth portion extending in the first direction and connected to another one of the second drain/source regions via a fourth contact, and the second wiring and the third wiring are provided between a sixth portion and the common gate electrode.*

\* \* \* \* \*